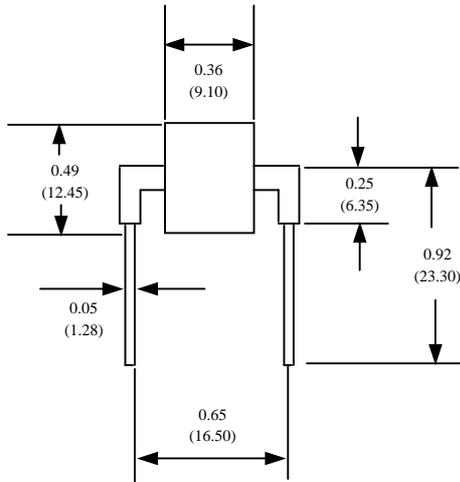


TransinK SERIES - TransinK-100M

(SILICON-AVALANCHE HIGH SURGE DIODES)



Dimensions in inches and (millimeters)

FEATURES

- Glass passivated chip junction
- 1000A surge capability at 8 x 20μsec waveform
(per IEC-61000-4-5)
- Excellent clamping capability
- Repetition rate (duty cycle) : 0.05 %
- Low incremental surge resistance
- Fast response time : typically less than 1.0μs
from 0 Volts to BV
- Operation temperature : -40 ~125
- Expoxy encapsulated has Underwriters Laboratory
Flammability Classification 94V-0

MECHANICAL DATA

Terminal : Ag Plated Axial leads,solderable per
MIL-STD-750,Method 2026

Mounting Position : Any

Weight : 0.188±0.019 ounces (5.340±0.534g)

RATING	SYMBOL	VALUE	UNITS
Breakdown voltage @ IT=1.0 mA	VBr	100±5%	Volt
Clamping Voltage @400A /10x1000 μ sec waveform	VC	135 max	Volt
Reverse Leakage @ 91.8V	IR	20 μ (max)	A

TransinK SERIES - TransinK - 100M

(SILICON-AVALANCHE HIGH SURGE DIODES)

Fig. 1 - Peak Pulse Power Rating Curve

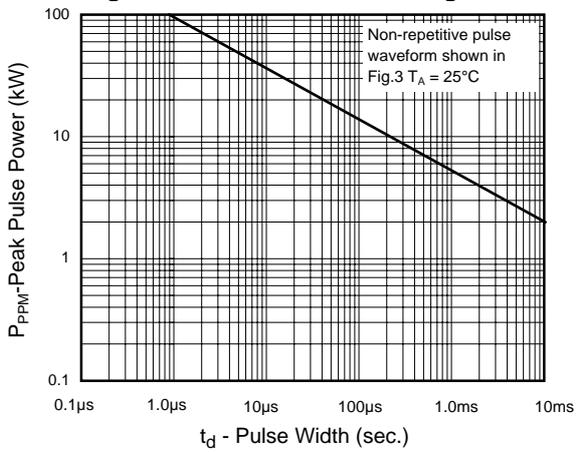


Fig.2 - Pulse Derating Curve

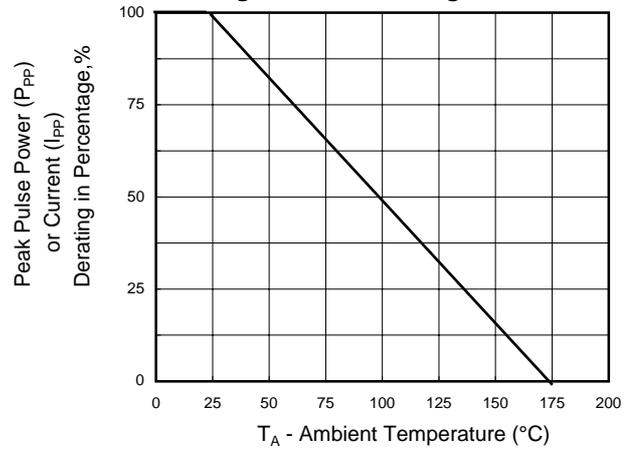


Fig.3 - Pulse Waveform

